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LXA03D530 Qspeed[™] Family

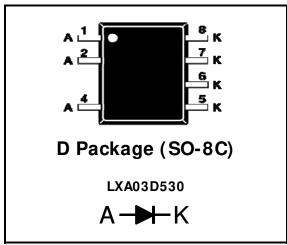


530 V, 3 A X-Series Diode

Product Summary

I _{F(AVG)}	3	Α
V_{RRM}	530	V
Q _{RR} (Typ at 125 °C)	75	nC
I _{RRM} (Typ at 125 °C)	3.2	Α
Softness t _B /t _A (Typ at 125 °C)	0.34	

Pin Assignment



RoHS Compliant

Package uses lead-free plating and green mold compound. Halogen-free per IEC 61249-2-21.

General Description

This device is an extremely low reverse recovery 530 V silicon diode. Its recovery characteristics increase efficiency, reduce EMI and eliminate snubbers.

Applications

- High-voltage power rectifier
- Power factor correction (PFC) boost diode
- Motor drive circuits
- DC-AC inverters

Features

- Low Q_{RR}, low I_{RRM}, low t_{RR}
- High dl_F/dt capable
- Soft recovery

Benefits

- Reduces peak reverse voltage
- Increases efficiency
 - Eliminates need for snubber circuits
 - Reduces EMI filter component size & count
- Enables extremely fast switching

Absolute Maximum Ratings

Absolute maximum ratings are the values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Symbol	Parameter	Conditions	Rating	Units
V_{RRM}	Peak repetitive reverse voltage	T _J = 25 °C	530	V
I _{F(AVG)}	Average forward current	$T_J = 150 ^{\circ}\text{C}, T_L = 29 ^{\circ}\text{C}$	3	Α
I _{FSM}	Non-repetitive peak surge current	60 Hz, ½ cycle, T _C = 25 °C	25	Α
I _{FSM}	Non-repetitive peak surge current	$1/2$ cycle of t = 28 μ s Sinusoid, T_C = 25 °C	350	Α
$T_{J(MAX)}$	Maximum junction temperature		150	°C
T _{STG}	Storage temperature		-55 to 150	°C
P_D	Power dissipation	T _L = 25 °C	4.6	W

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Thermal Resistance

Symbol	Resistance	Conditions	Rating	Units
$R_{\theta JA}$	Junction to ambient	Soldered to 1 sq. in. (645 mm ²), 2 oz. Cu.	80	°C/W
$R_{\theta JL}$	Junction to lead	Lead temperature measured on pin 7	27	°C/W

Electrical Specifications at $T_J = 25$ °C (unless otherwise specified)

	Liectrical Specifications at 1j= 25°C (unless otherwise specified)						
Symbol	Parameter	Conditions		Min	Тур	Max	Units
DC Chara	acteristics						
	Deverse augment	$V_R = 530 \text{ V}, T_J = 25 \text{ °C}$		-	0.4	250	μΑ
I _R	Reverse current	V _R = 530 V, T _J = 125 °C		-	0.275	-	mA
V_{F}	Forward voltage	I _F = 3 A, T _J = 25 °C		-	1.55	1.71	V
VF	Forward voltage	I _F = 3 A, T _J = 150 °C		-	1.33	-	٧
CJ	Junction capacitance	V _R = 10 V, 1 MHz		-	15	-	pF
Dynamic	Characteristics						
	Reverse recovery time	$dI/dt = 200 \text{ A/}\mu\text{s}$ V_R = 400 V, I_F = 3 A	T _J = 25 °C	-	25	34.3	ns
t _{RR}			T _J = 125 °C	-	33	-	ns
0	D	dI/dt = 200 A/μs	T _J = 25 °C	-	39	55	nC
Q_{RR}	Reverse recovery charge	V_{R} = 400 V, I_{F} = 3 A	T _J = 125 °C	-	75	-	nC
1	Maximum reverse	dI/dt = 200 A/μs	T _J = 25 °C	-	2.2	-	Α
I _{RRM}	recovery current $V_R = 400 \text{ V}, I_F = 3 \text{ A}$	T _J = 125 °C	-	3.2	-	Α	
S Softness f	Softness factor = $\frac{t_B}{}$	dI/dt = 200 A/μs	T _J = 25 °C	-	0.7	-	
	Softhess factor = ${t_A}$	$V_R = 400 \text{ V}, I_F = 3 \text{ A}$	T _J = 125 °C	-	0.34	-	

Note to component engineers: X-Series diodes employ Schottky technologies in their design and construction. Therefore, component engineers should plan their test setups to be similar to those for traditional Schottky test set-ups. (For additional details, see Application Note AN-300.)

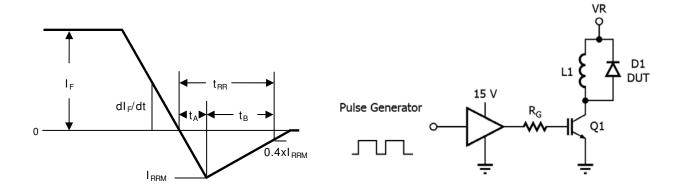


Figure 1. Reverse Recovery Definitions.

Figure 2. Reverse Recovery Test Circuit.



PI-7614-041315

Electrical Specifications at $T_J = 25$ °C (unless otherwise specified) 0.9 0.8 T₃ = 125 °C 0.6 (A) # 4 **Y** 0.5 0.4 0.3 0.2 0.1 0.0 0.0 0.5 2.0 1.2 $V_F(V)$ Figure 3. Typical I_F vs. V_{F.} Figure 4. Typical I_F vs. V_{F.} 60 50 ر الع الع الع 20 10 0 1 80 100 120 50 75 100 125 Lead Temperature, T_L (°C) $V_R(V)$ Figure 5. Typical C_J vs. V_{R.} Figure 6. DC Current Derating Curve. 160 45 140 40 $dI_r/dt = 500 A/\mu s$ 120 35 100 30 (JE 80 20 tag (ns) **8** 60 15 40 10 20 IF (A) Figure 7. Typical Q_{RR} vs. I_F at T_J = 125 °C.

Figure 8. Typical t_{RR} vs. I_F at T_J = 125 °C.

Electrical Specifications at $T_J = 25$ °C (unless otherwise specified)

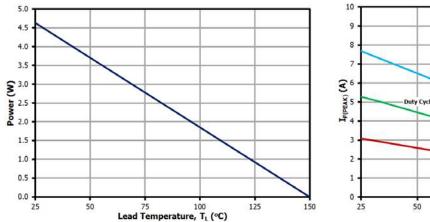


Figure 9. Power Derating Curve.

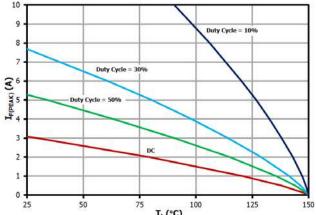


Figure 10. I_F (Peak) vs. T_L , f = 70 kHz.

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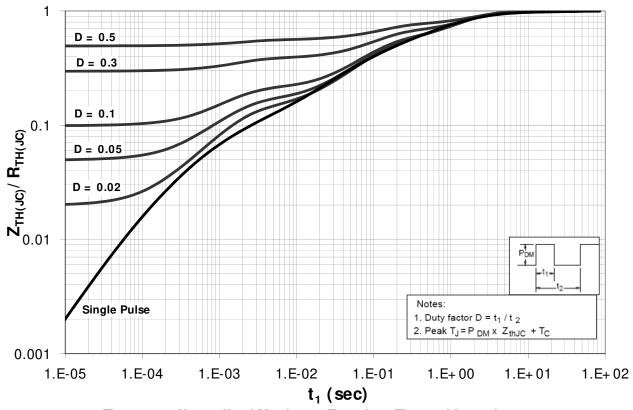
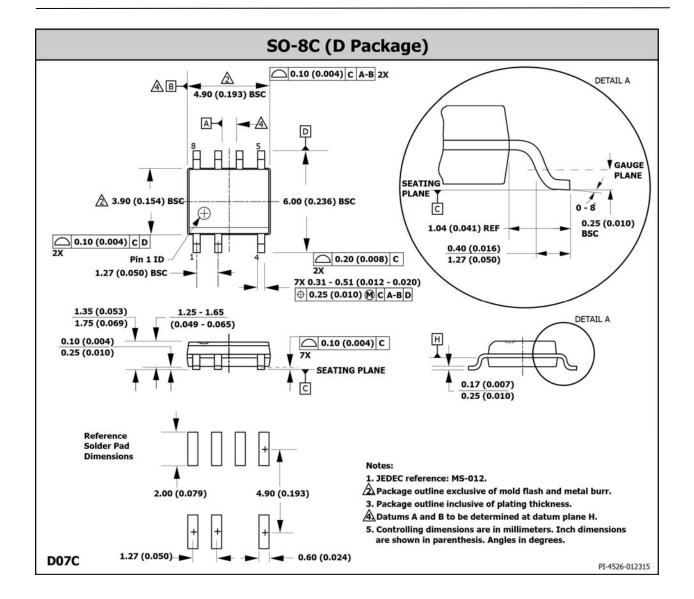


Figure 11. Normalized Maximum Transient Thermal Impedance.



Ordering Information

Part Number	Package	Packing
LXA03D530	SO-8C	2500 units/reel

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LXA03D530

Revision	Notes	Date
1.0	Initial Release.	04/15



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